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FERAM CELL WITH INTERNAL OXYGEN SOURCE
AND METHOD OF OXYGEN RELEASE

ABSTRACT OF THE DISCLOSURE

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An integrated ferroelectric/CMOS structure which comprises at least a ferroelectric material, a pair of electrodes in contact with opposite surfaces of the ferroelectric material, where the electrodes do not decompose at

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deposition or annealing, and an oxygen source layer in contact with at least one of said electrodes, said oxygen source layer being a metal oxide which at least partially decomposes during deposition and/or subsequent processing is provided as well as a method of fabricating the same.

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